

V_{DSS}	650V
$R_{DS(on)}$ (Typ.)	80mΩ
I_D^{*1}	30A
P_D	134W

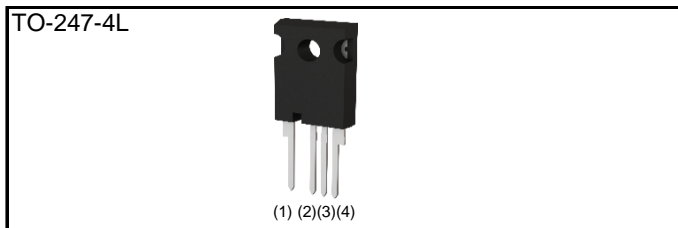
●Features

- 1) Qualified to AEC-Q101
- 2) Low on-resistance
- 3) Fast switching speed
- 4) Fast reverse recovery
- 5) Easy to parallel
- 6) Simple to drive
- 7) Pb-free lead plating ; RoHS compliant

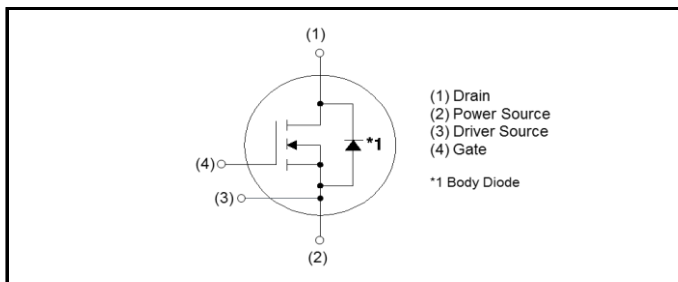
●Application

- Automobile
- Switch mode power supplies

●Outline



●Inner circuit



Please note Driver Source and Power Source are not exchangeable. Their exchange might lead to malfunction.

●Packaging specifications

Type	Packing	Tube
	Reel size (mm)	-
	Tape width (mm)	-
	Basic ordering unit (pcs)	30
	Taping code	C15
	Marking	SCT3080AR

●Absolute maximum ratings ($T_{vj} = 25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit	
Drain - Source Voltage	V_{DSS}	650	V	
Continuous Drain current	$T_c = 25^{\circ}\text{C}$	I_D^{*1}	30	A
	$T_c = 100^{\circ}\text{C}$	I_D^{*1}	21	A
Pulsed Drain current ($T_c = 25^{\circ}\text{C}$)	$I_{D,pulse}^{*2}$	75	A	
Gate - Source voltage (DC)	V_{GSS}	-4 to +22	V	
Gate - Source surge voltage ($t_{surge} < 300\text{ns}$)	$V_{GSS,surge}^{*3}$	-4 to +26	V	
Recommended drive voltage	$V_{GS,op}^{*4}$	0 / +18	V	
Virtual Junction temperature	T_{vj}	175	$^{\circ}\text{C}$	
Range of storage temperature	T_{stg}	-55 to +175	$^{\circ}\text{C}$	

●Electrical characteristics (T_{vj} = 25°C unless otherwise specified)

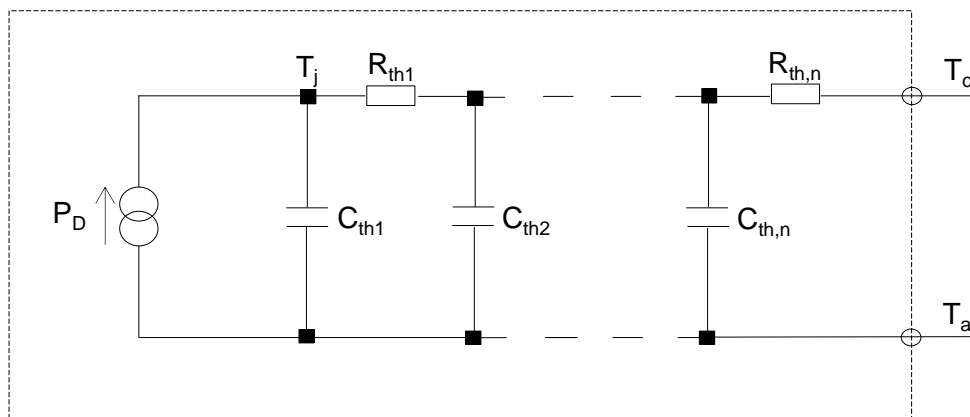
Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 1mA T _{vj} = 25°C T _{vj} = -55°C	650 650	- -	- -	V
Zero Gate voltage Drain current	I _{DSS}	V _{GS} = 0V, V _{DS} = 650V T _{vj} = 25°C T _{vj} = 150°C	- -	1 2	10 -	μA
Gate - Source leakage current	I _{GSS+}	V _{GS} = +22V, V _{DS} = 0V	-	-	100	nA
Gate - Source leakage current	I _{GSS-}	V _{GS} = -4V, V _{DS} = 0V	-	-	-100	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} = 10V, I _D = 5mA	2.7	-	5.6	V
Static Drain - Source on - state resistance	R _{DS(on)} ^{*5}	V _{GS} = 18V, I _D = 10A T _{vj} = 25°C T _{vj} = 150°C	- -	80 115	104 -	mΩ
Gate input resistance	R _G	f = 1MHz, open drain	-	13	-	Ω

●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - case	R _{thJC}	-	0.86	1.12	K/W

●Typical Transient Thermal Characteristics

Symbol	Value	Unit	Symbol	Value	Unit
R _{th1}	1.14×10 ⁻¹	K/W	C _{th1}	5.02×10 ⁻⁴	Ws/K
R _{th2}	5.07×10 ⁻¹		C _{th2}	4.91×10 ⁻³	
R _{th3}	2.51×10 ⁻¹		C _{th3}	4.99×10 ⁻²	



● **Electrical characteristics** ($T_{vj} = 25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Transconductance	g_{fs}^{*5}	$V_{DS} = 10\text{V}, I_D = 10\text{A}$	-	3.8	-	S
Input capacitance	C_{iss}	$V_{GS} = 0\text{V}$	-	571	-	pF
Output capacitance	C_{oss}	$V_{DS} = 500\text{V}$	-	39	-	
Reverse transfer capacitance	C_{rss}	$f = 1\text{MHz}$	-	19	-	
Effective output capacitance, energy related	$C_{o(er)}$	$V_{GS} = 0\text{V}$ $V_{DS} = 0\text{V to } 300\text{V}$	-	99	-	pF
Total Gate charge	Q_g^{*5}	$V_{DS} = 300\text{V}$ $I_D = 10\text{A}$	-	48	-	nC
Gate - Source charge	Q_{gs}^{*5}	$V_{GS} = 18\text{V}$	-	10	-	
Gate - Drain charge	Q_{gd}^{*5}	See Fig. 1-1.	-	25	-	
Turn - on delay time	$t_{d(on)}^{*5}$	$V_{DS} = 400\text{V}$ $I_D = 15\text{A}$	-	4	-	ns
Rise time	t_r^{*5}	$V_{GS} = 0\text{V}/+18\text{V}$	-	14	-	
Turn - off delay time	$t_{d(off)}^{*5}$	$R_G = 0\Omega, L = 750\mu\text{H}$ $L_\sigma = 50\text{nH}, C_\sigma = 10\text{pF}$	-	15	-	
Fall time	t_f^{*5}	See Fig. 2-1, 2-2, 2-3.	-	13	-	
Turn - on switching loss	E_{on}^{*5}	E_{on} includes diode reverse recovery.	-	77	-	μJ
Turn - off switching loss	E_{off}^{*5}		-	15	-	

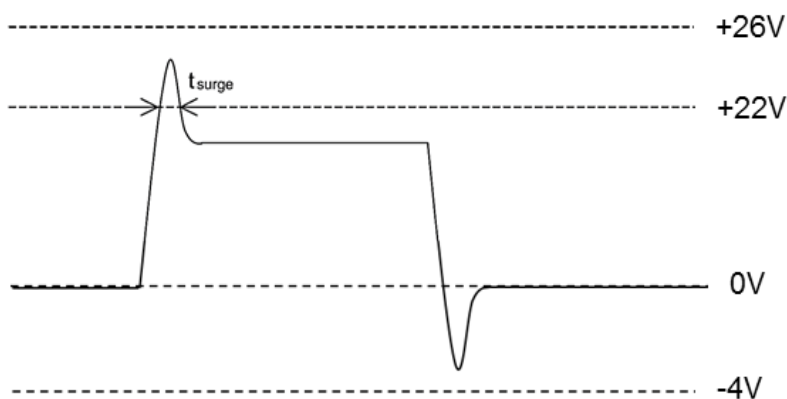
● **Body diode electrical characteristics** (Source-Drain) ($T_{vj} = 25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Body diode continuous, forward current	I_S *1	$T_c = 25^{\circ}\text{C}$	-	-	30	A
Body diode direct current, pulsed	I_{SM} *2		-	-	75	A
Forward voltage	V_{SD} *5	$V_{GS} = 0\text{V}, I_S = 10\text{A}$	-	3.2	-	V
Reverse recovery time	t_{rr} *5	$I_F = 10\text{A}$ $V_R = 400\text{V}$	-	18	-	ns
Reverse recovery charge	Q_{rr} *5	$di/dt = 2500\text{A}/\mu\text{s}$	-	254	-	nC
Peak reverse recovery current	I_{rrm} *5	$L_{\sigma} = 50\text{nH}, C_{\sigma} = 10\text{pF}$ See Fig. 3-1, 3-2.	-	23	-	A

*1 Limited by maximum T_{vj} and for Max. R_{thJC} .

*2 $PW \leq 10\mu\text{s}$, Duty cycle $\leq 1\%$

*3 Example of acceptable V_{GS} waveform



Please note especially when using driver source that V_{GSS_surge} must be in the range of absolute maximum rating.

*4 Please be advised not to use SiC-MOSFETs with V_{GS} below 13V as doing so may cause thermal runaway.

*5 Pulsed

●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

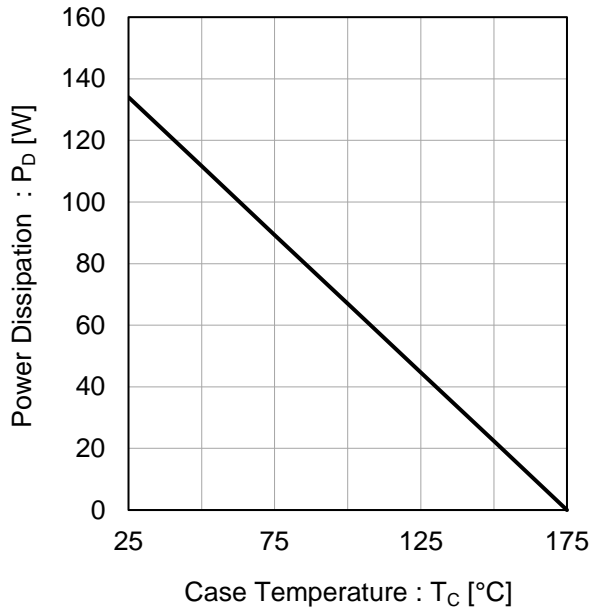


Fig.2 Maximum Safe Operating Area

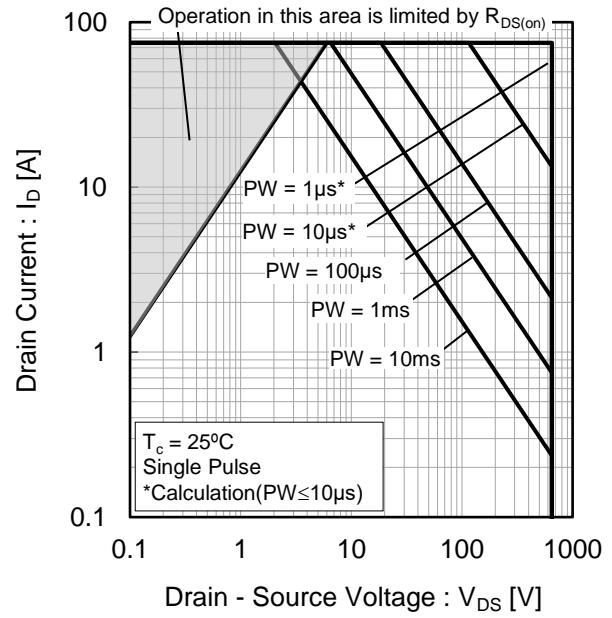
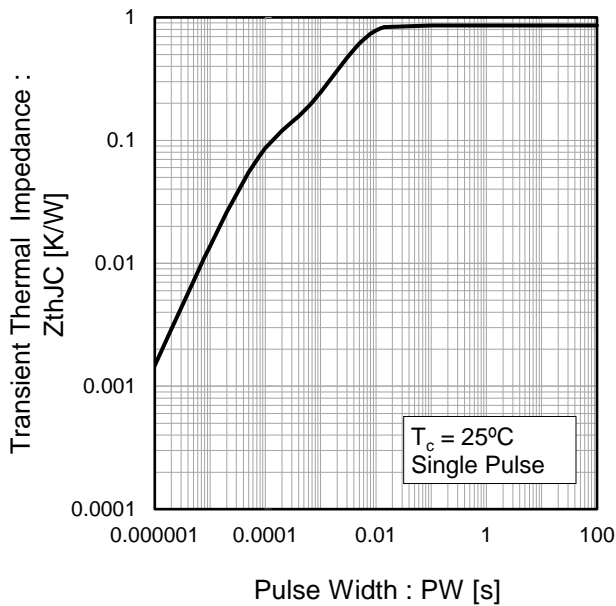


Fig.3 Typical Transient Thermal Impedance vs. Pulse Width



●Electrical characteristic curves

Fig.4 Typical Output Characteristics(I)

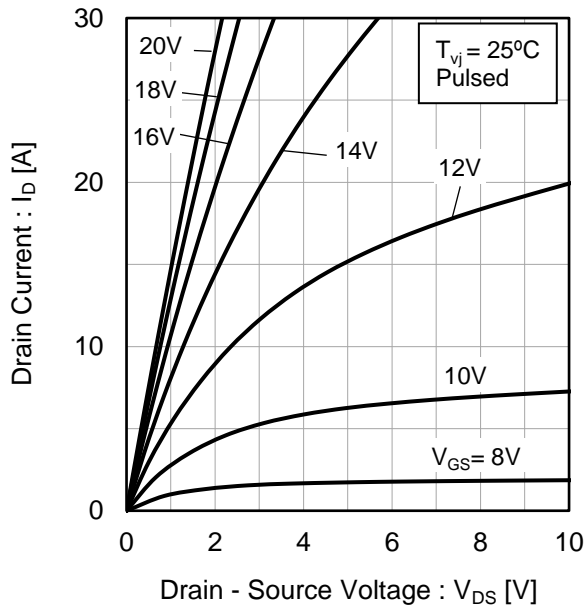


Fig.5 Typical Output Characteristics(II)

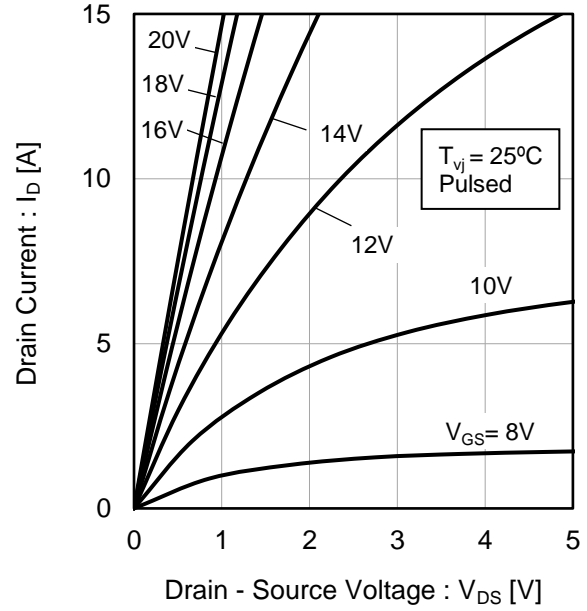
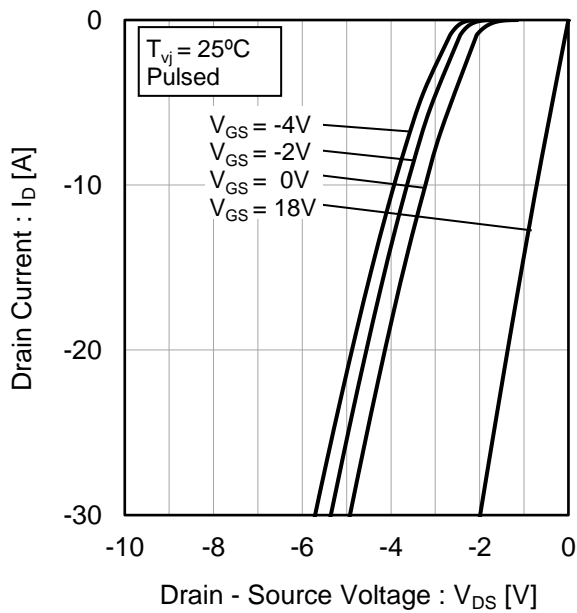


Fig.6 $T_{vj} = 25^\circ\text{C}$ 3rd Quadrant Characteristics



●Electrical characteristic curves

Fig.7 $T_{vj} = 150^{\circ}\text{C}$ Typical Output Characteristics(I)

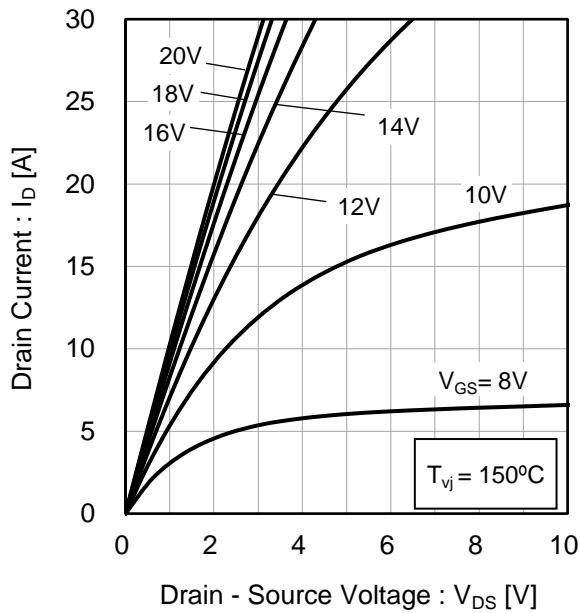


Fig.8 $T_{vj} = 150^{\circ}\text{C}$ Typical Output Characteristics(II)

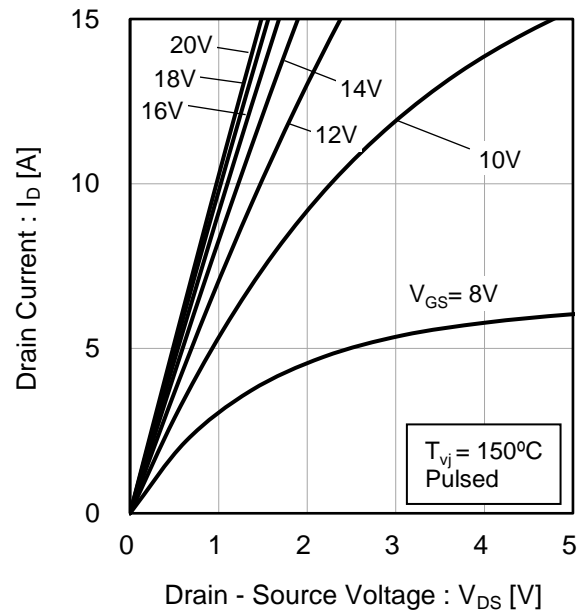


Fig.9 $T_{vj} = 150^{\circ}\text{C}$ 3rd Quadrant Characteristics

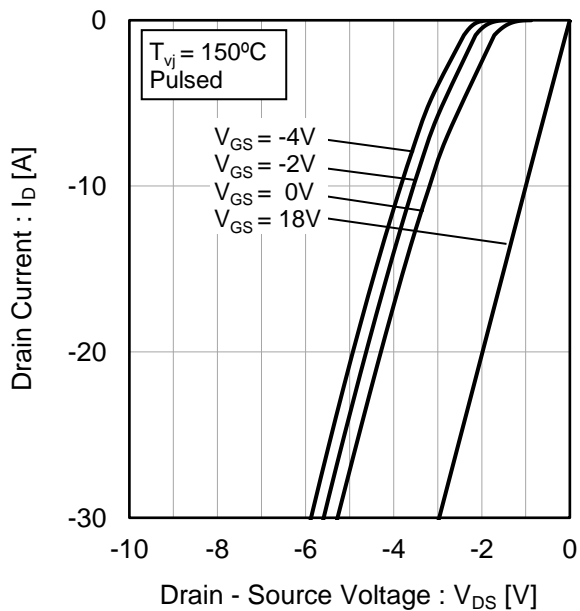
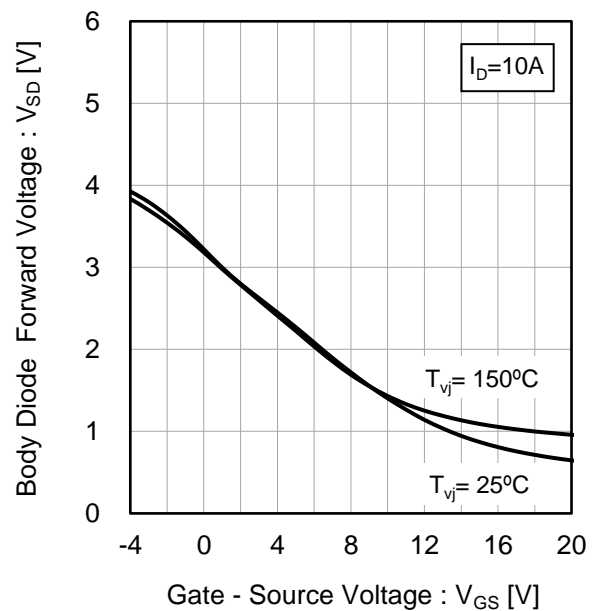


Fig.10 Body Diode Forward Voltage vs. Gate - Source Voltage



●Electrical characteristic curves

Fig.11 Typical Transfer Characteristics (I)

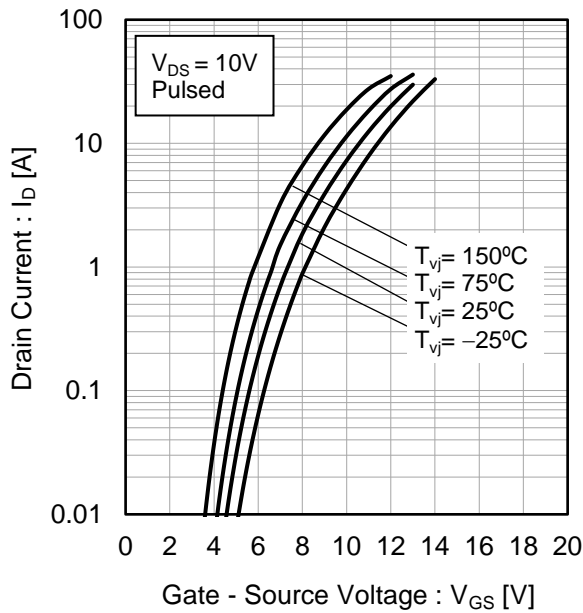


Fig.12 Typical Transfer Characteristics (II)

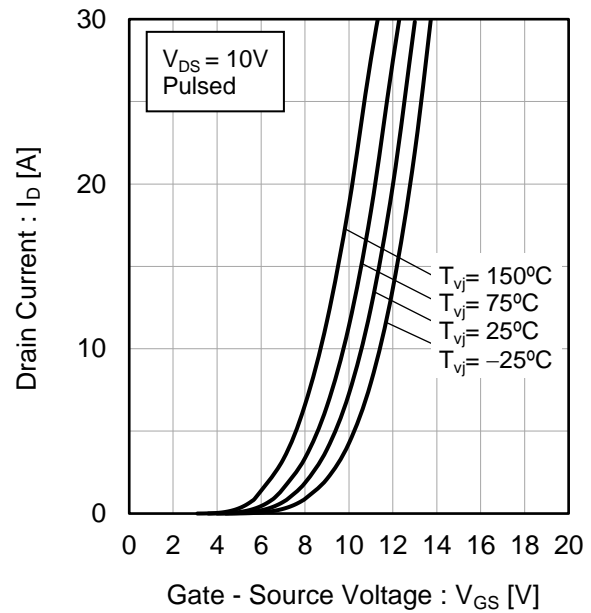


Fig.13 Gate Threshold Voltage vs. Virtual Junction Temperature

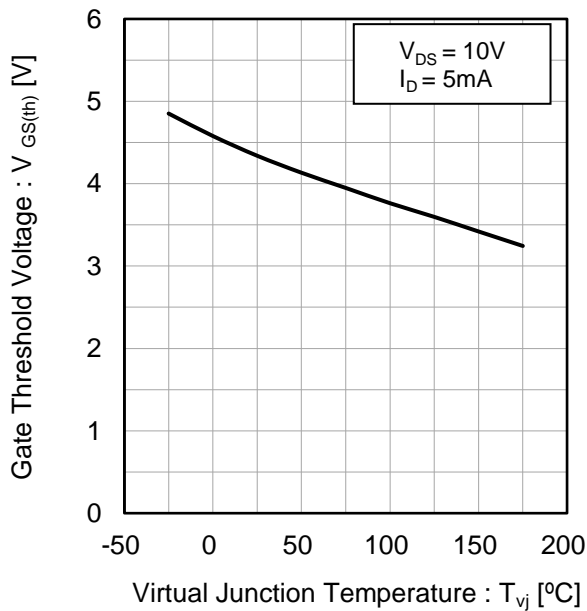
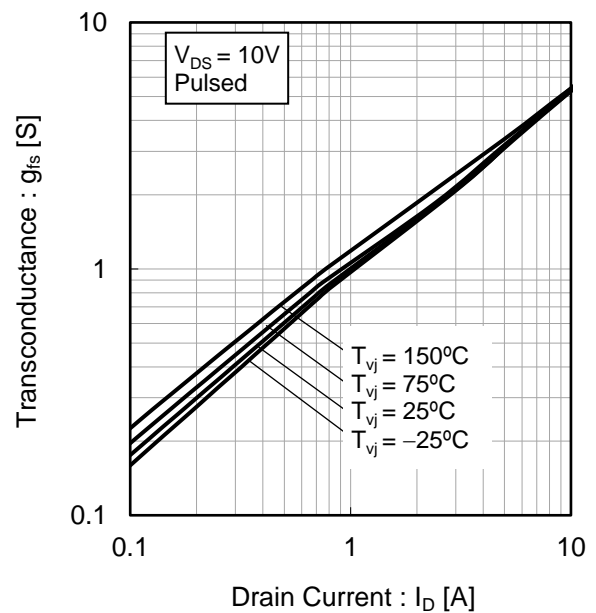


Fig.14 Transconductance vs. Drain Current



●Electrical characteristic curves

Fig.15 Static Drain - Source On - State Resistance vs. Gate - Source Voltage

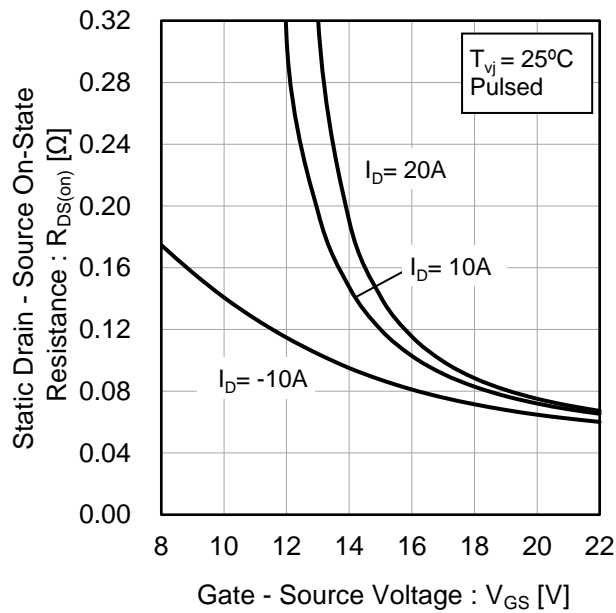


Fig.16 Static Drain - Source On - State Resistance vs. Virtual Junction Temperature

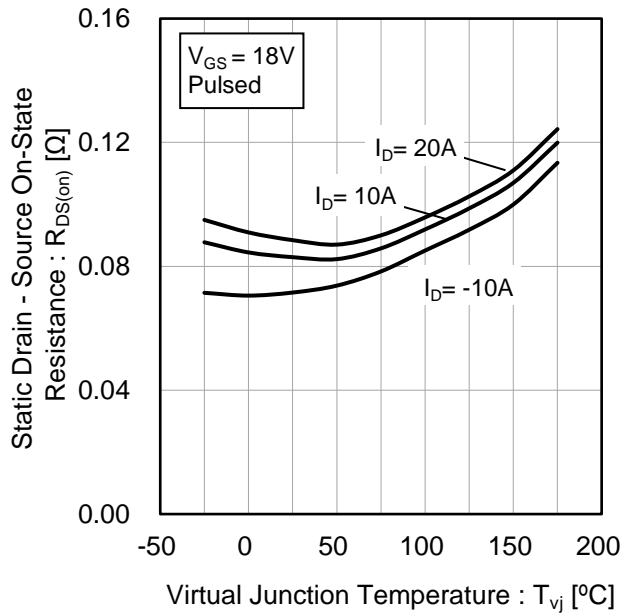


Fig.17 Static Drain - Source On - State Resistance vs. Drain Current

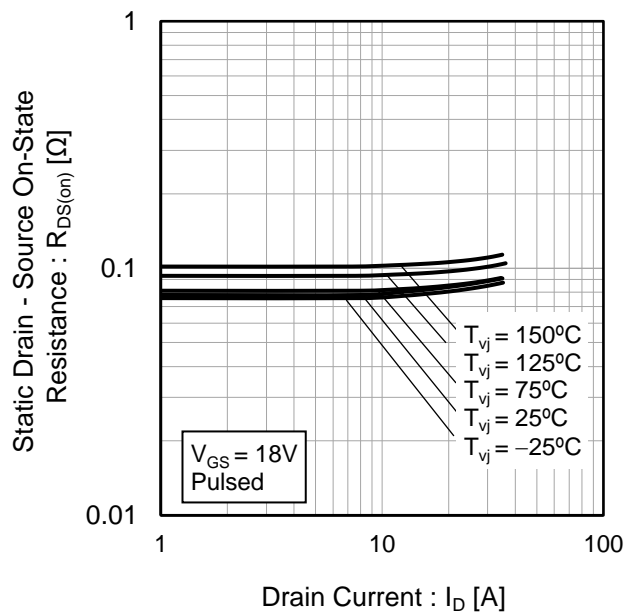
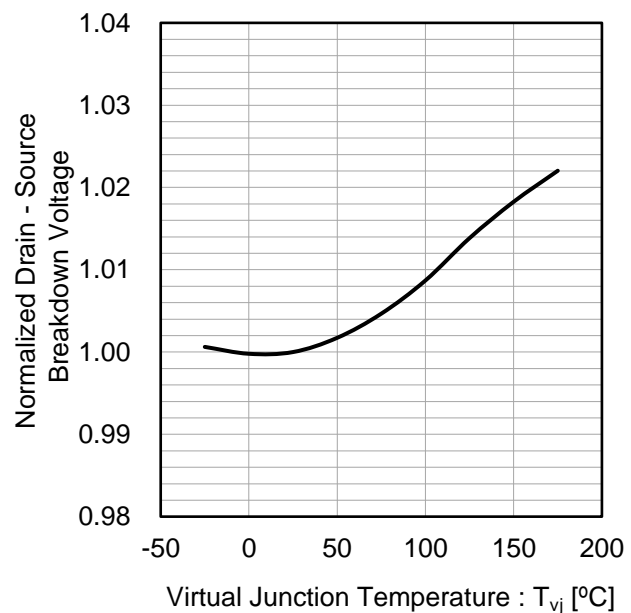


Fig.18 Normalized Drain - Source Breakdown Voltage vs. Virtual Junction Temperature



●Electrical characteristic curves

Fig.19 Typical Capacitance vs. Drain - Source Voltage

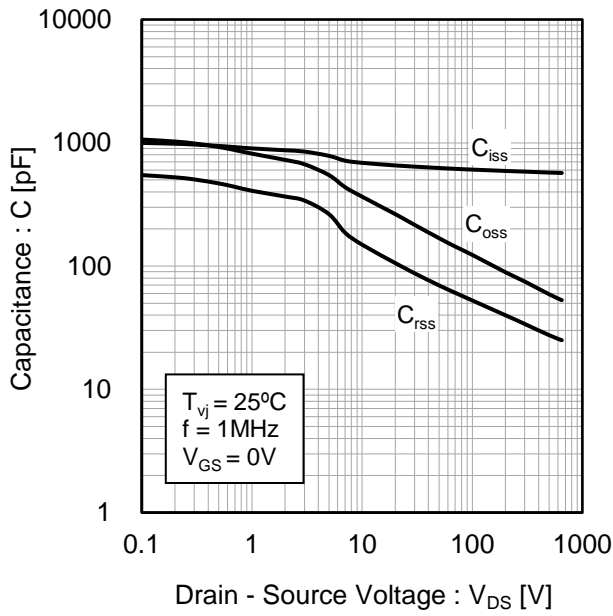


Fig.20 C_{oss} Stored Energy

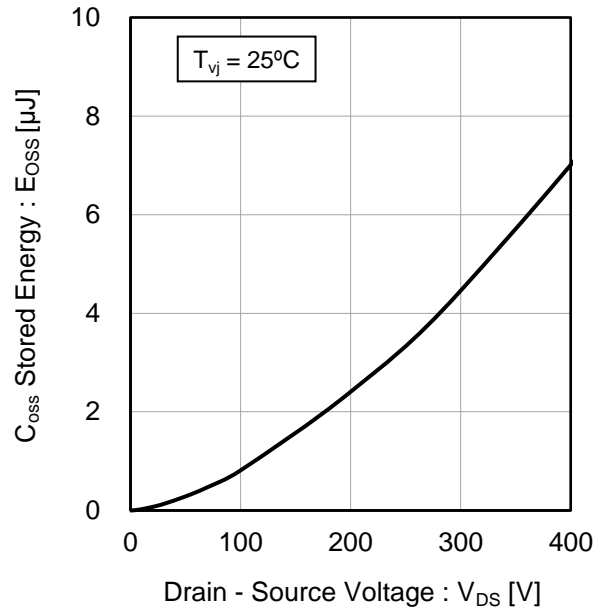
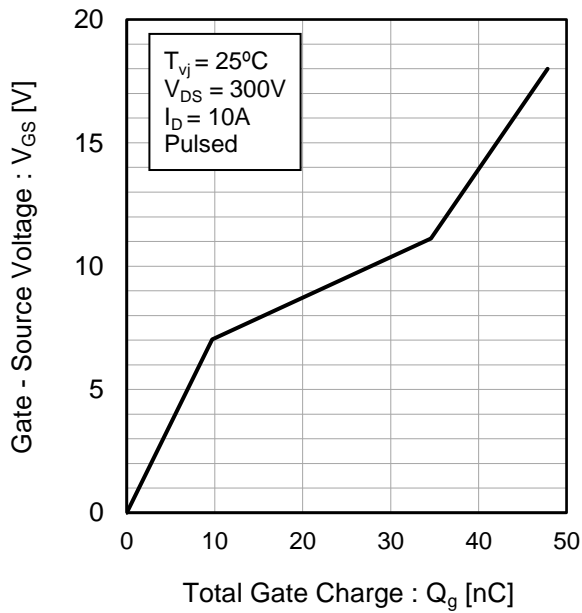
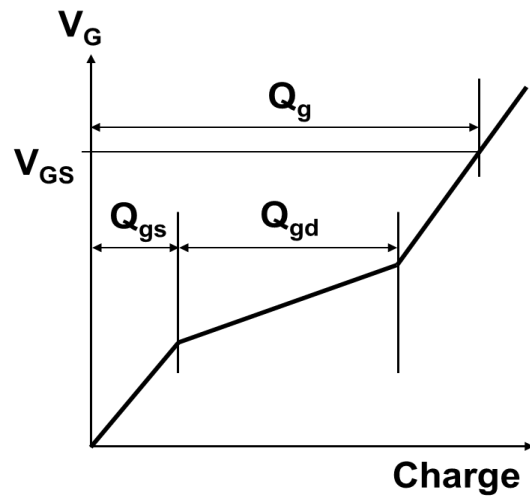


Fig.21 Dynamic Input Characteristics



*Gate Charge Waveform



●Electrical characteristic curves

Fig.22 Typical Switching Time vs. External Gate Resistance

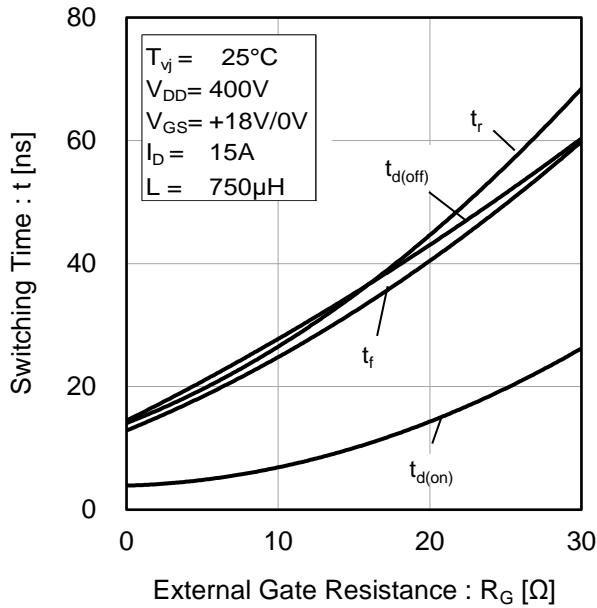


Fig.23 Typical Switching Loss vs. Drain - Source Voltage

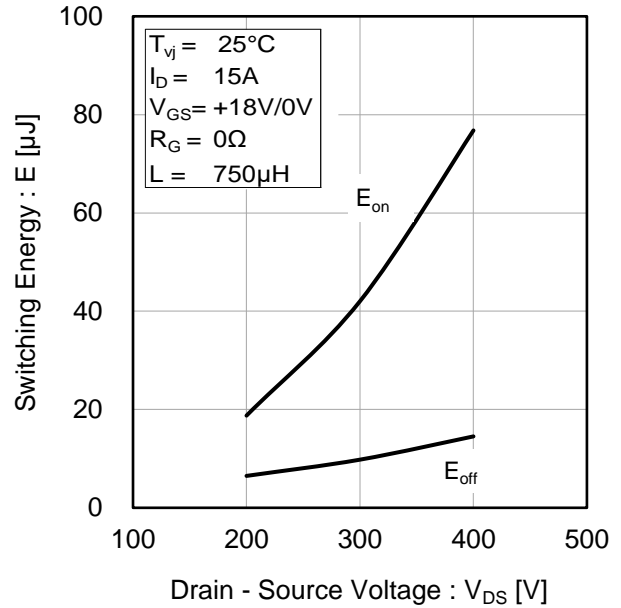


Fig.24 Typical Switching Loss vs. Drain Current

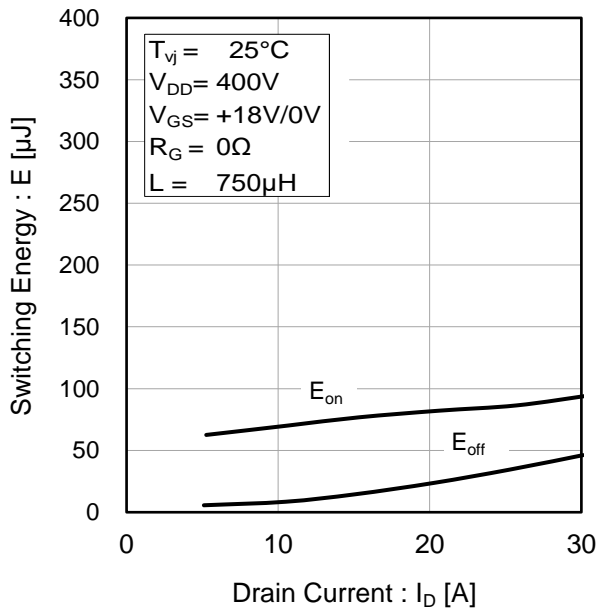
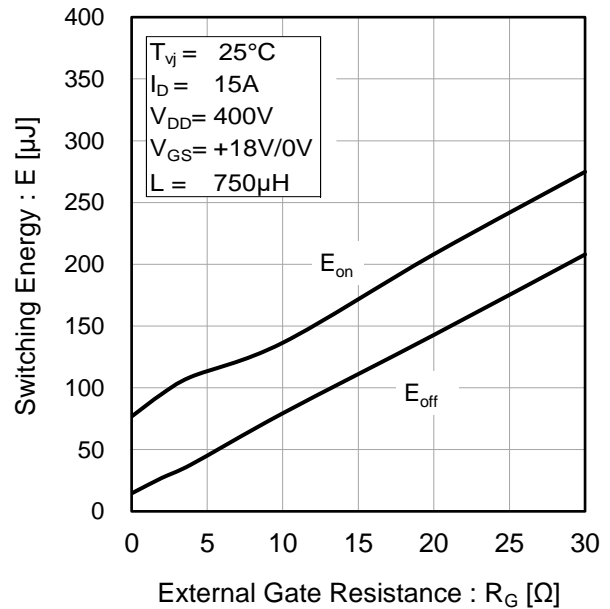


Fig.25 Typical Switching Loss vs. External Gate Resistance



● Measurement circuits and waveforms

Fig.1-1 Gate Charge Measurement Circuit

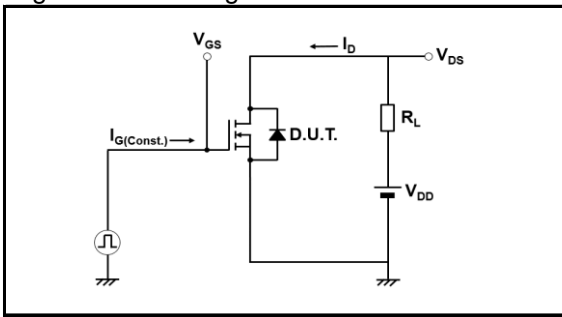


Fig.2-1 Switching Characteristics Measurement Circuit

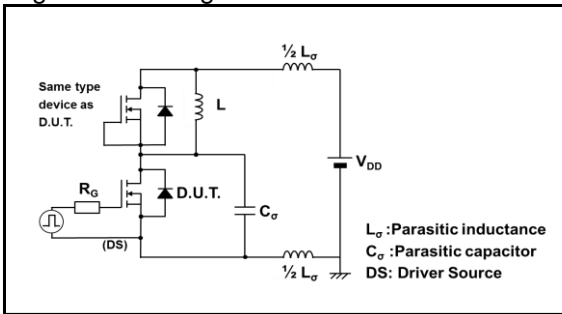


Fig.2-2 Waveforms for Switching Time

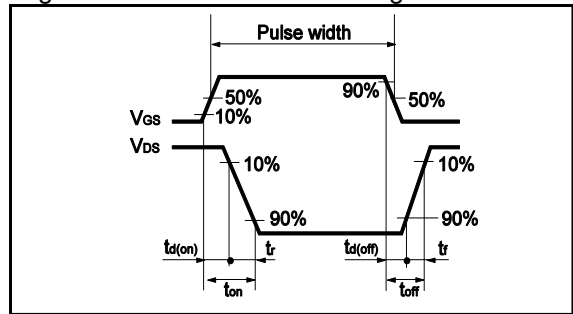


Fig.2-3 Waveforms for Switching Energy Loss

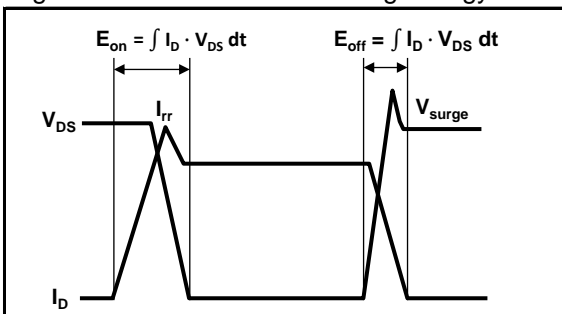


Fig.3-1 Reverse Recovery Time Measurement Circuit

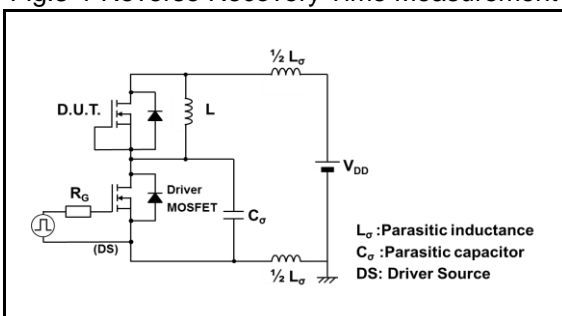
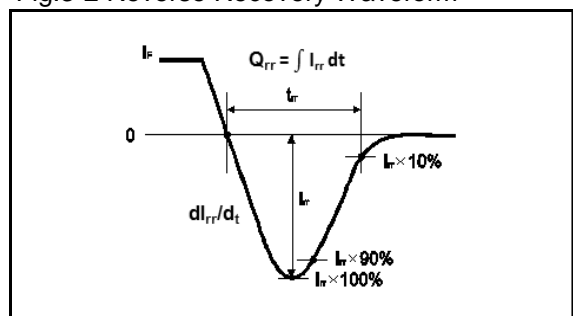
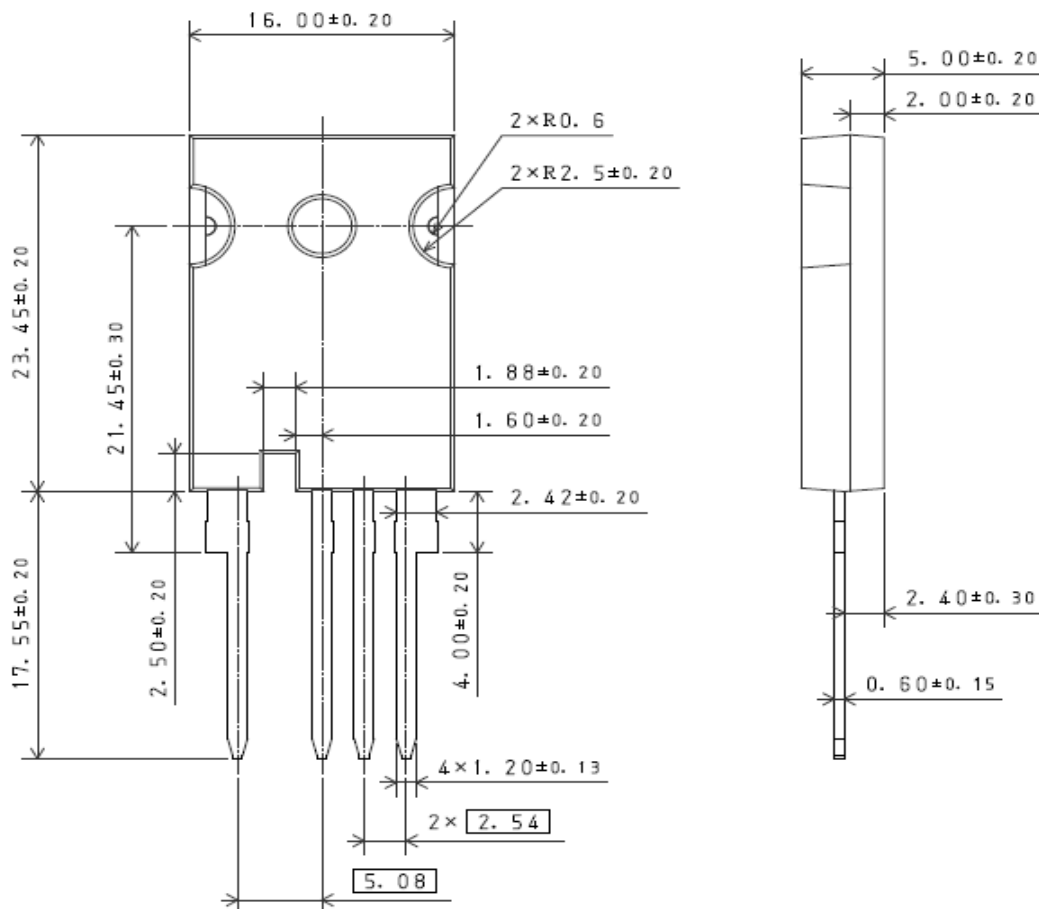


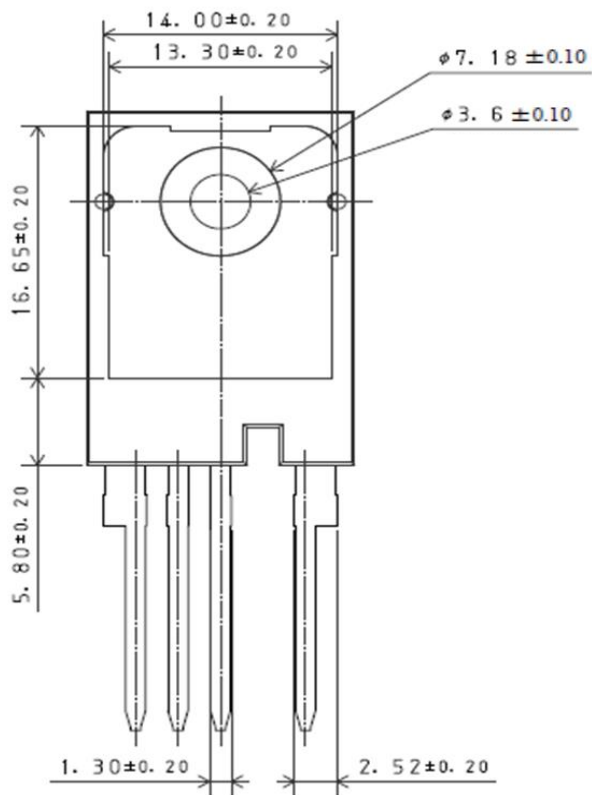
Fig.3-2 Reverse Recovery Waveform



●Package Dimensions

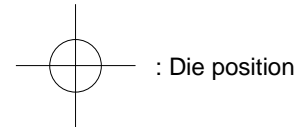
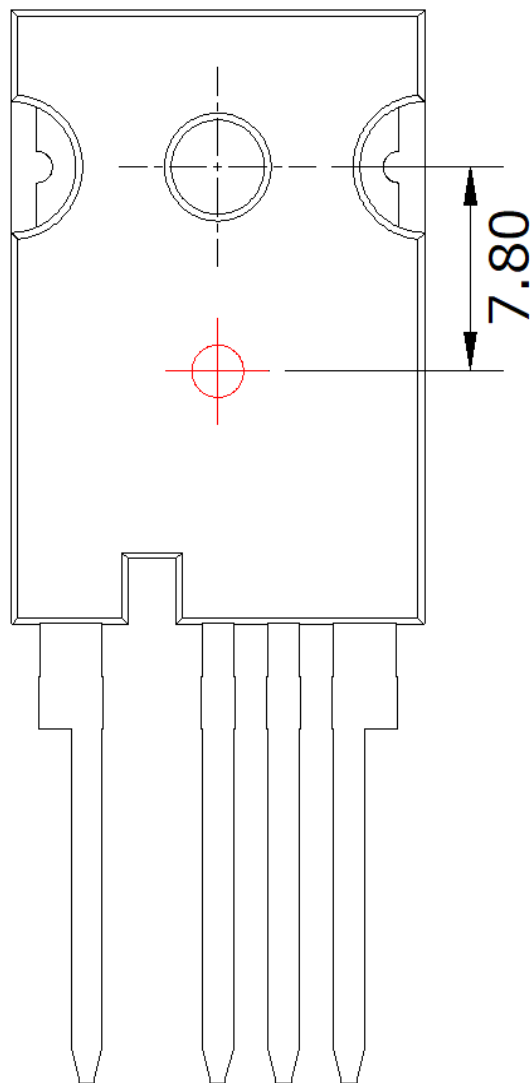


Unit: mm



Unit: mm

● Die Bonding Layout



- Front view of the packaging.
- Dimensions are design values.
- If the heat sink is to be installed, it should be in contact with the die bonding point.

Unit: mm

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[G3R40MT12J](#)